

MOSFET - Power, Single N-Channel, SO8-FL

30 V, 0.62 mΩ, 433 A



ON Semiconductor®

www.onsemi.com

NTMFS0D6N03C

Features

- Advanced Package (5x6mm) with Excellent Thermal Conduction
- Ultra Low $R_{DS(on)}$ to Improve System Efficiency
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- ORing
- Motor Drive
- Power Load Switch
- Battery Management and Protection

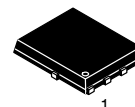
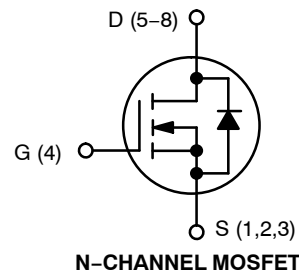
MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V _{DSS}	30	V	
Gate-to-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current R _{θJC} (Note 2)	Steady State	T _C = 25°C	I _D	433	A
		T _C = 100°C		306	
Power Dissipation R _{θJC} (Note 2)	Steady State	T _C = 25°C	P _D	200	W
Continuous Drain Current R _{θJA} (Notes 1, 2)		T _A = 25°C	I _D	60	A
		T _A = 100°C		42	
Power Dissipation R _{θJA} (Notes 1, 2)	T _A = 25°C	P _D	3.9	W	
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs	I _{DM}	900	A	
Source Current (Body Diode)		I _S	156	A	
Single Pulse Drain-to-Source Avalanche Energy (I _L = 45.4 A _{pk})		E _{AS}	1032	mJ	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

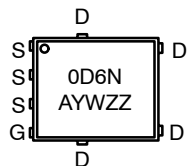
1. Surface-mounted on FR4 board using 1 in² pad, 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

V _{(BR)DSS}	R _{DS(ON) MAX}	I _{D MAX}
30 V	0.62 mΩ @ 10 V	433 A
	0.9 mΩ @ 4.5 V	



DFN5 (SO-8FL)
CASE 506EZ

MARKING DIAGRAMS



- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTMFS0D6N03C

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	0.8	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	38	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	134	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		12		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 280\ \mu\text{A}$	1.3		2.2	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 280\ \mu\text{A}$, ref to 25°C		-5.7		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.52	0.62	m Ω
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		0.72	0.9	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 3\text{ V}, I_D = 30\text{ A}$		150		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$		0.4		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V}, f = 1\text{ MHz}$		10500		pF
Output Capacitance	C_{OSS}			5740		
Reverse Transfer Capacitance	C_{RSS}			161		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		65		nC
Threshold Gate Charge	$Q_{G(TH)}$			16		
Gate-to-Drain Charge	Q_{GD}			12		
Gate-to-Source Charge	Q_{GS}			27		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		145		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}, R_G = 3.0\ \Omega$		24		ns
Rise Time	t_r			12		
Turn-Off Delay Time	$t_{d(OFF)}$			89		
Fall Time	t_f			19		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$	0.75	1.2	V
			$T_J = 125^\circ\text{C}$	0.60		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, V_{DS} = 15\text{ V}, I_S = 30\text{ A}$		97		ns
Reverse Recovery Charge	Q_{RR}			135		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

NTMFS0D6N03C

TYPICAL CHARACTERISTICS

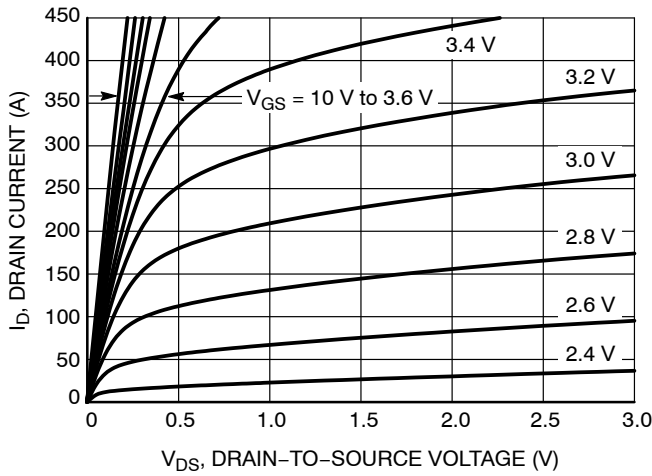


Figure 1. On-Region Characteristics

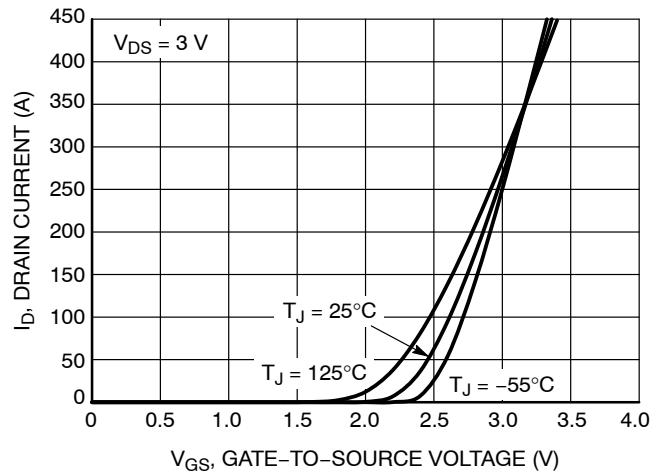


Figure 2. Transfer Characteristics

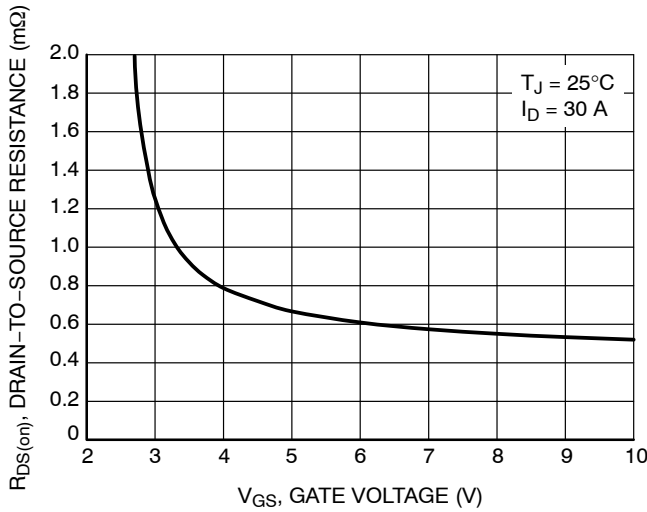


Figure 3. On-Resistance vs. Gate-to-Source Voltage

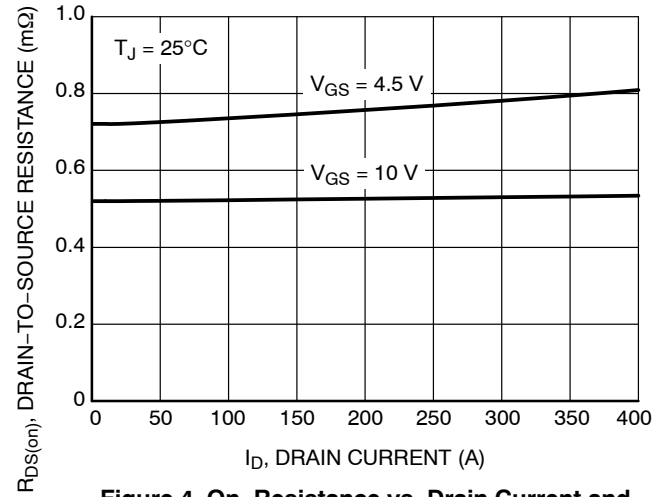


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

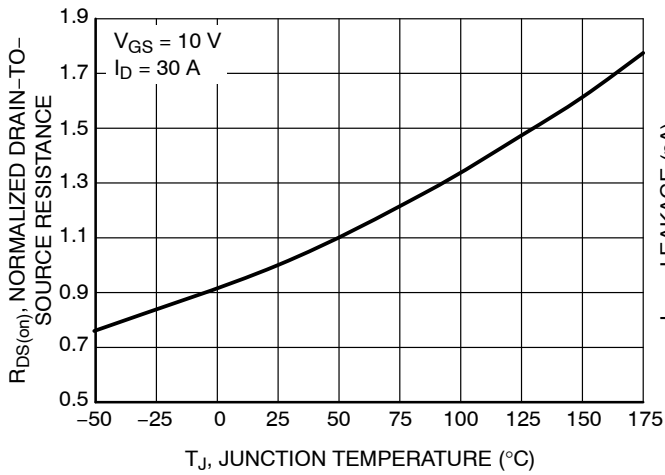


Figure 5. On-Resistance Variation with Temperature

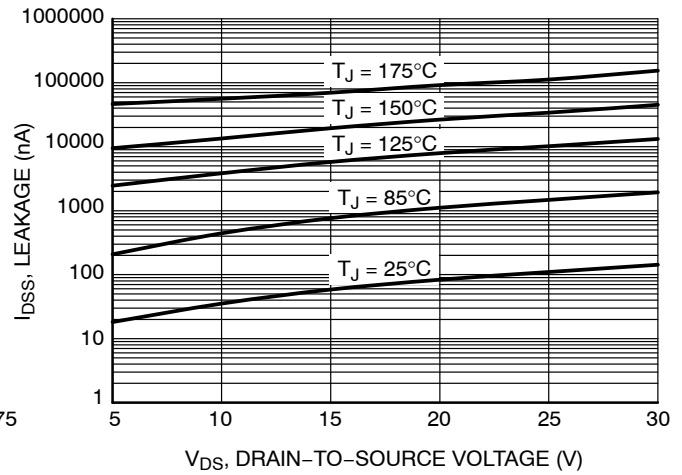


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTMFS0D6N03C

TYPICAL CHARACTERISTICS

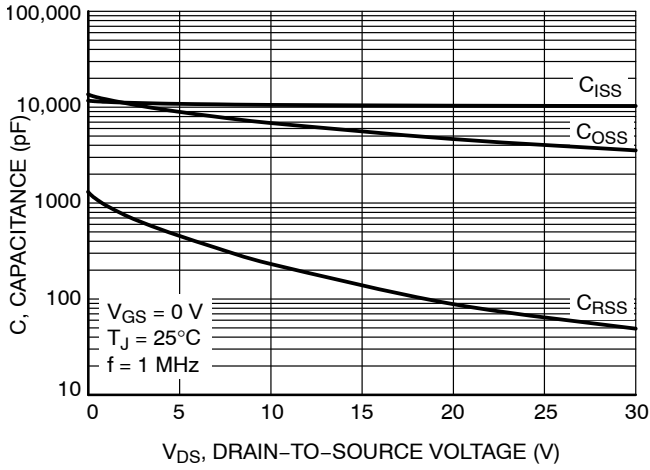


Figure 7. Capacitance Variation

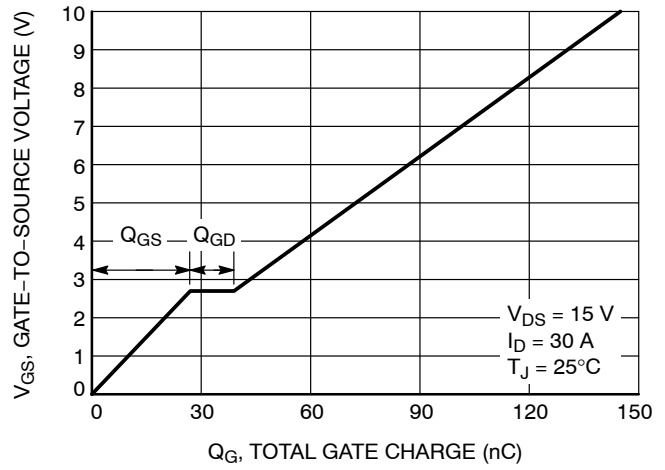


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

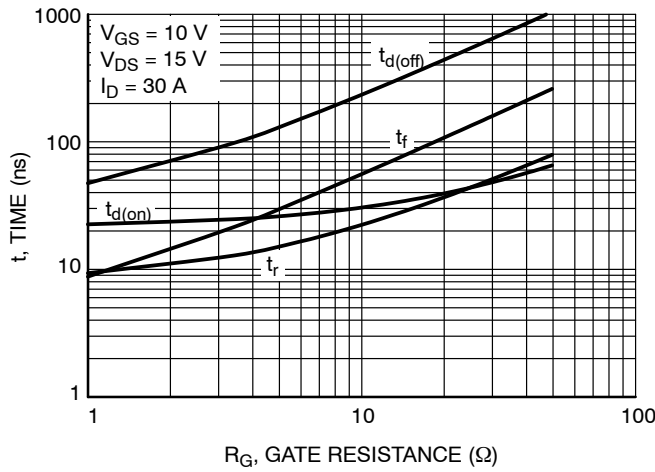


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

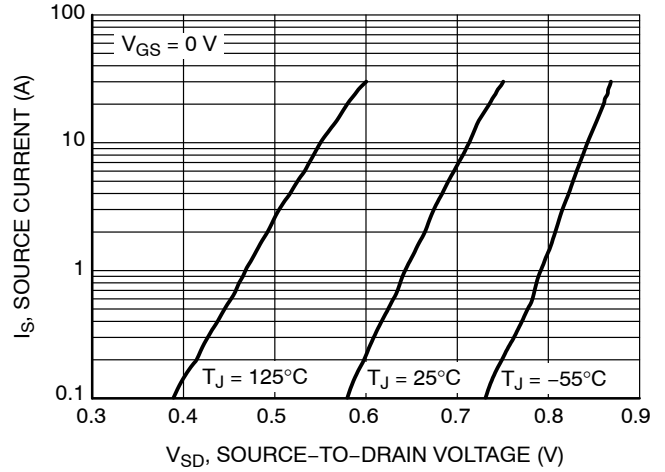


Figure 10. Diode Forward Voltage vs. Current

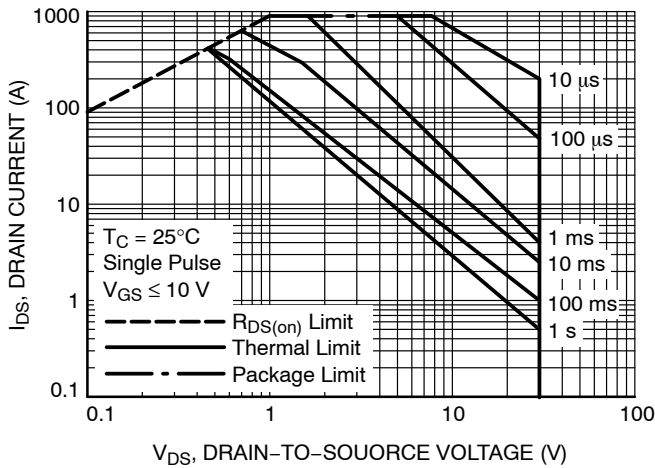


Figure 11. Safe Operating Area

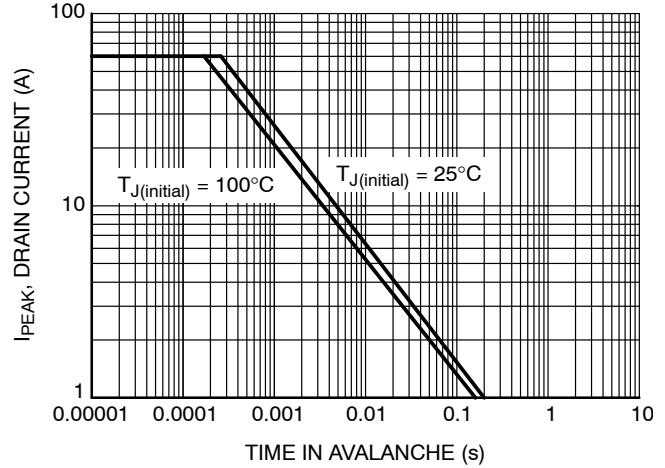


Figure 12. I_{PEAK} vs. Time in Avalanche

NTMFS0D6N03C

TYPICAL CHARACTERISTICS

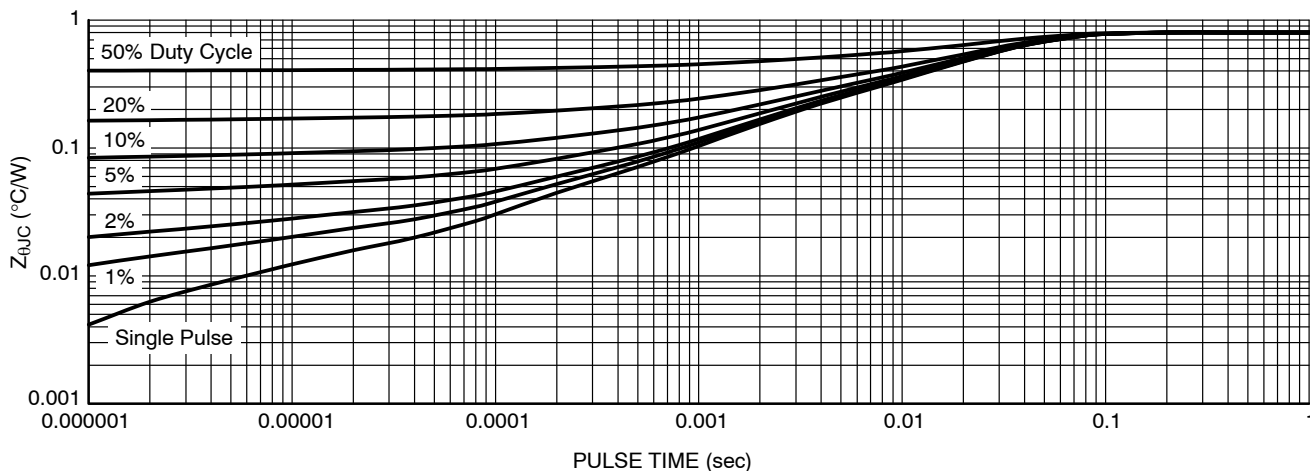


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

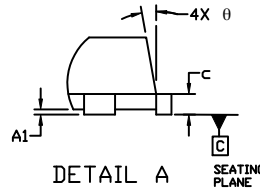
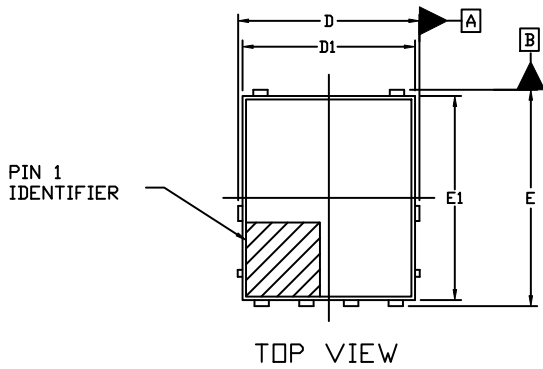
Device	Marking	Package	Shipping [†]
NTMFS0D6N03CT1G	0D6N	DFN5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFS0D6N03C

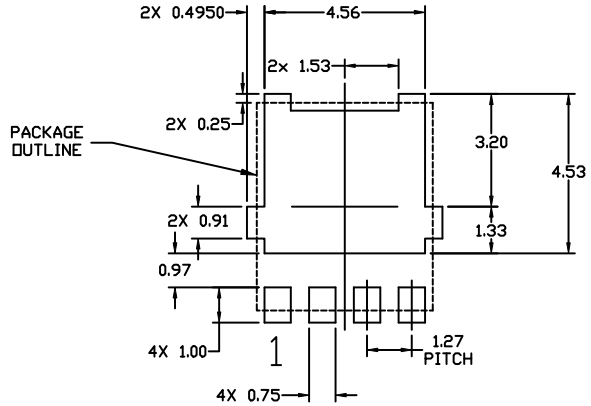
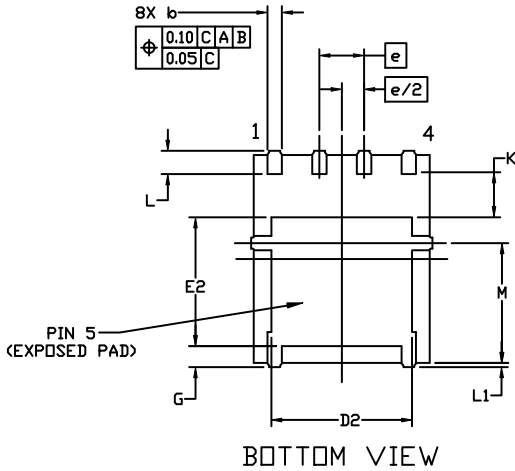
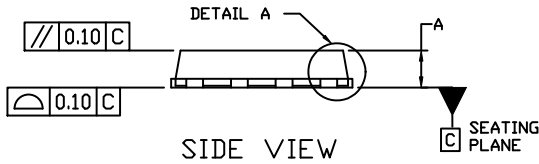
PACKAGE DIMENSIONS

DFN5 5x6, 1.27P (SO-8FL)
CASE 506EZ
ISSUE O



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
k	1.10	1.20	1.40
L	0.51	0.575	0.71
L1	1.25 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative